CE 3110 Electronic Devices Laboratory (1 semester credit hour) Laboratory to accompany CE 3310. Experimental determination and illustration of properties of carriers in semiconductors including carrier drift, carrier diffusion; p-n junctions including forward and reverse bias effects and transient effects; bipolar transistors including the Ebers-Moll model and secondary effects; field effect transistors including biasing effects, MOS capacitance and threshold voltage. Corequisite: CE 3310 or EE 3310. Prerequisite: RHE T 1302. (Same as EE 3110) (0-3) S